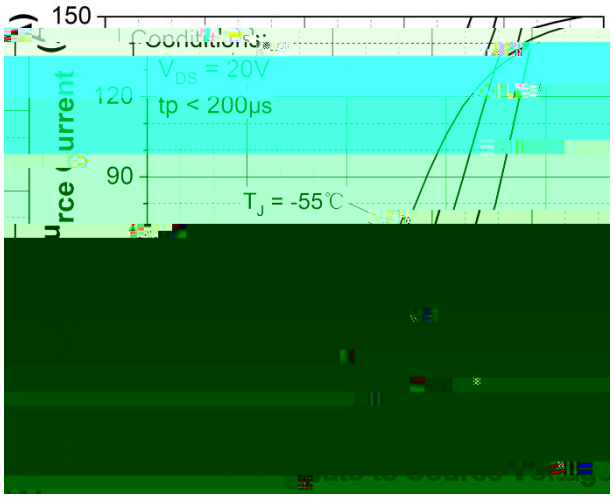
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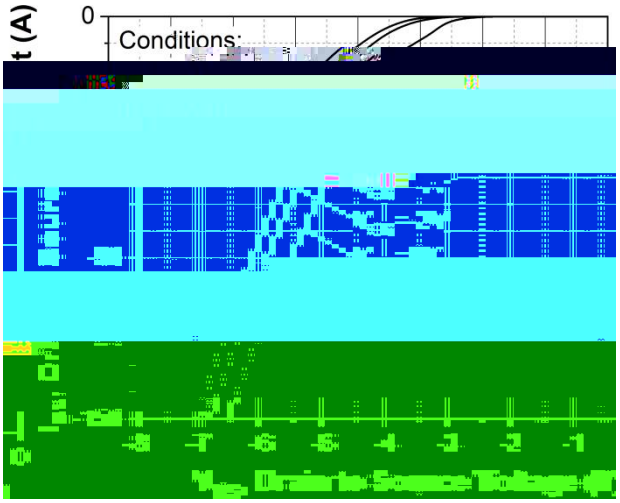
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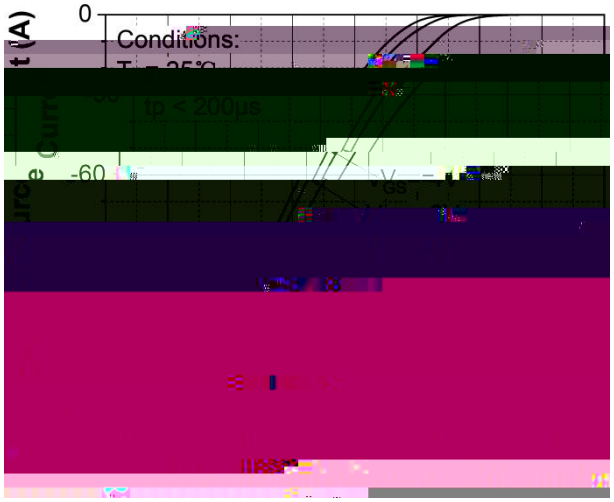
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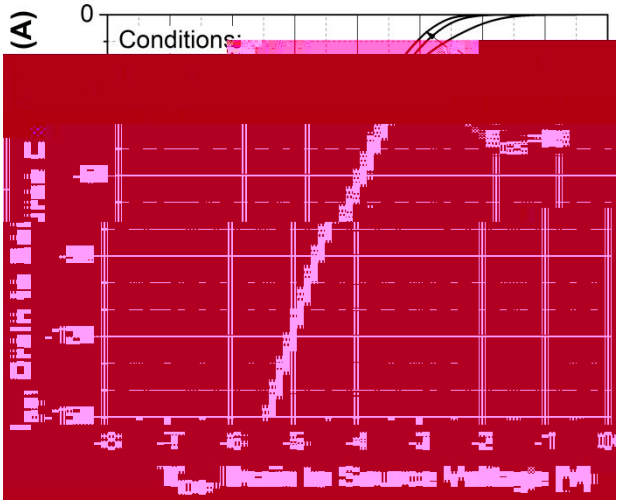
ñ>M° ø(rAe e f9 Đ

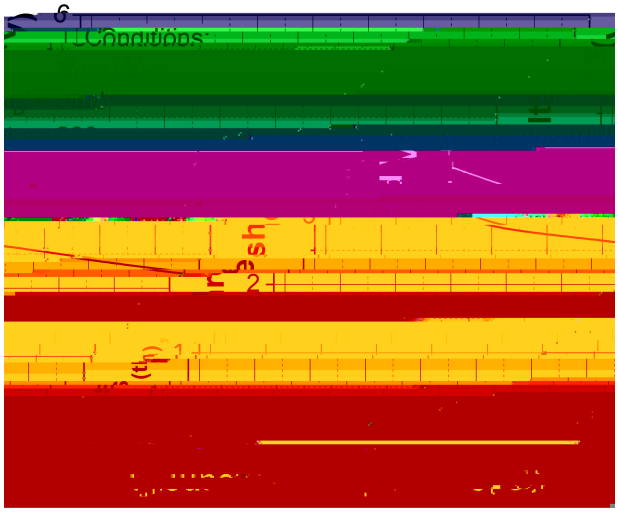


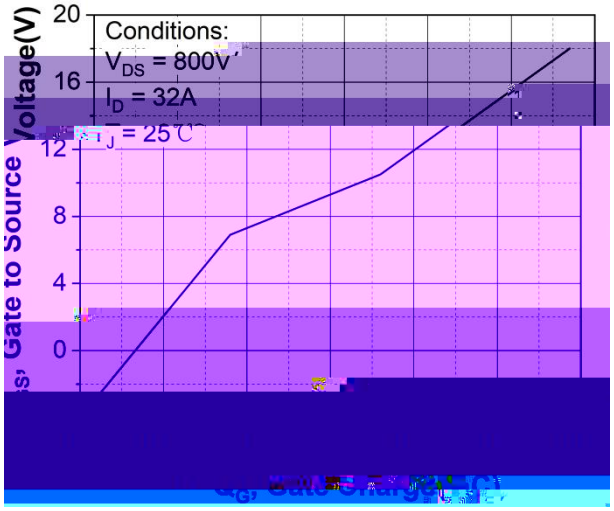

150
120
90
Conditions:
V_{DS} = 20V
tp < 200μs
T_J = -55℃

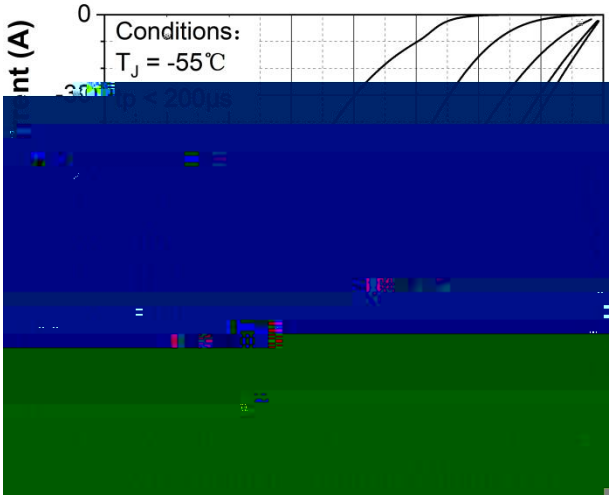

0
Conditions:

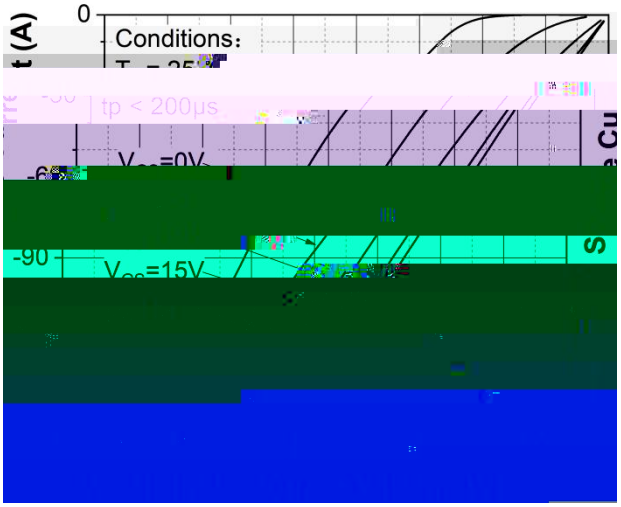

0
Conditions:
tp < 200μs
-60

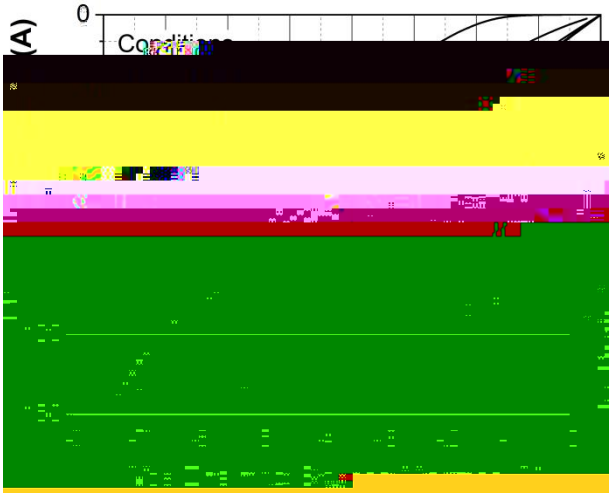

0
Conditions:

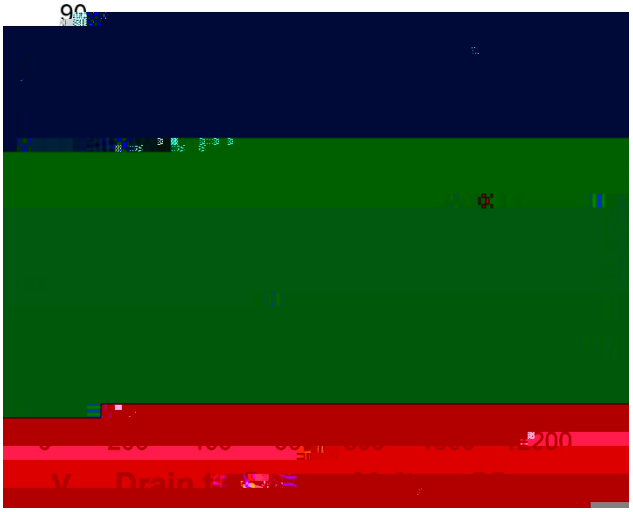

Conditions:
2
1

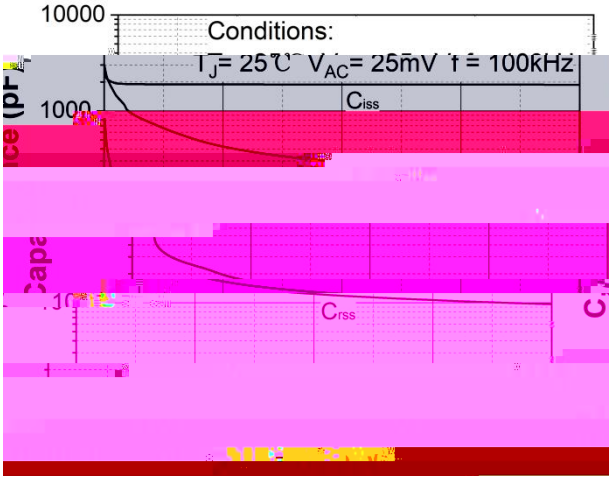

20
16
12
8
4
0
Conditions:
V_{DS} = 800V
I_D = 32A
T_J = 25℃

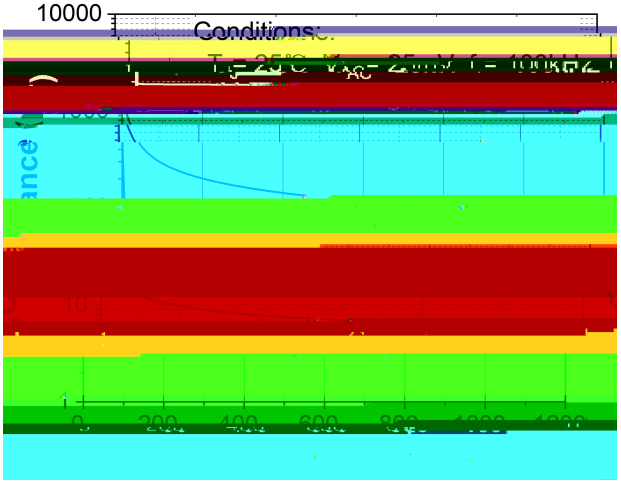

0
Conditions:
T_J = -55℃
tp < 200μs

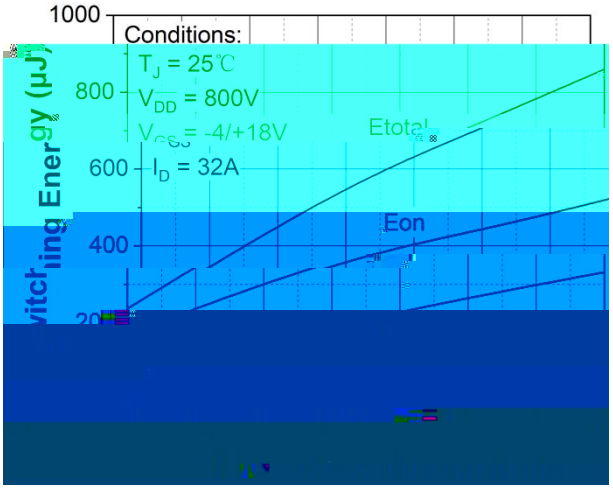

0
Conditions:
tp < 200μs
-90

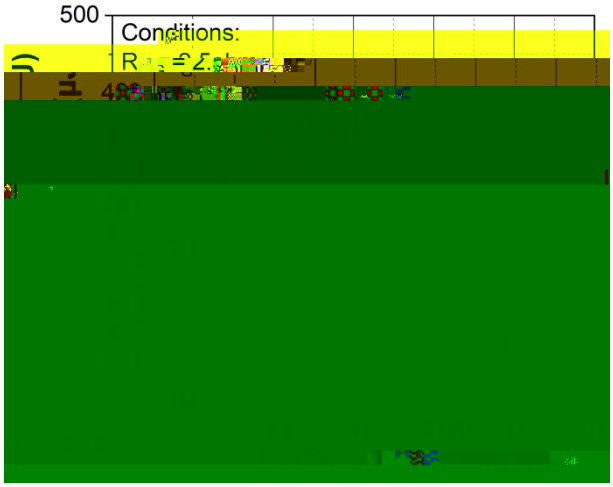

0

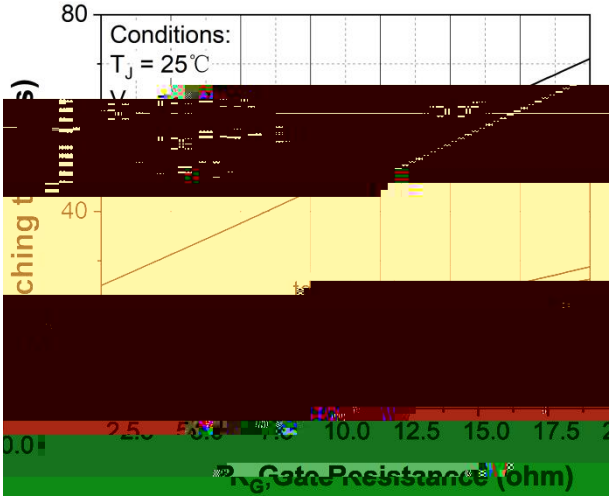

90

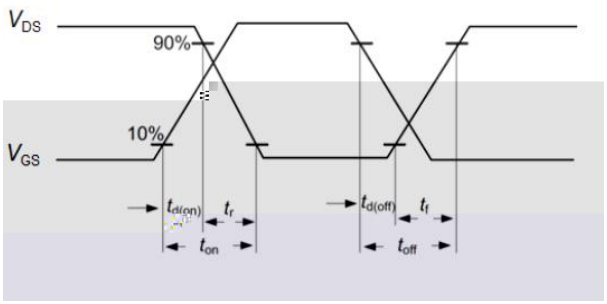

10000
Conditions:
T_J= 25℃ V_{AC}= 25mV f = 100kHz
1000
C_{iss}
C_{rss}

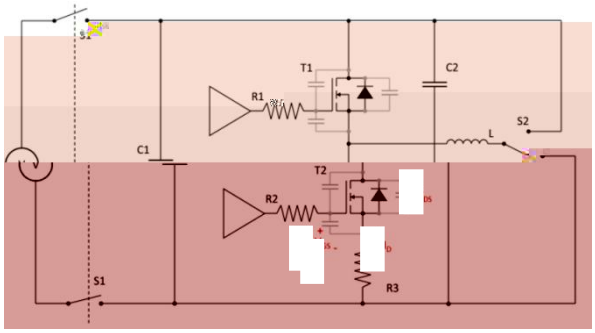

10000
Conditions:
1000
10
1

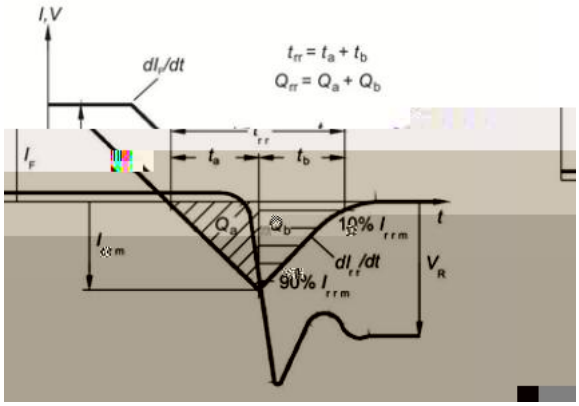

1000
Conditions:
T_J = 25℃
V_{DD} = 800V
V_{GS} = -4/+18V
I_D = 32A
800
600
400
Etotal
Eon
Energy (μJ)


500
Conditions:


80
Conditions:
T_J = 25℃
40
10.0
12.5
15.0
17.5
Gate Resistance (ohm)


V_{DS}
90%
10%
V_{GS}
$t_{d(on)}$
t_r
t_{on}
$t_{d(off)}$
t_f
t_{off}


S2
T1
C2
R1
S2
L
C1
T2
R2
R3
S1


I,V
dI_F/dt
$t_{rr} = t_a + t_b$
$Q_{rr} = Q_a + Q_b$
I_F
t_a
t_b
Q_a
Q_b
10% I_{rrm}
t
I_{rrm}
dI_{rr}/dt
90% I_{rrm}
V_R

			——